IGD8233 Series

High Reliability Isolated Dual-Channel Gate Driver

IGD8233 is 4.0A sourcing and 6.0A sinking peak output current with rail-to-rail dual-channel isolated gate driver. It includes the programmable deadtime and DIS for disabling the output. The driver can be configured as dual high/low side or half bridge driver. It has 5kVRMS isolation in SOW16 package. The high CMTI, low propagation delay features perfectly suite the high speed MOSFET, IGBT and SiC gate driver applications.

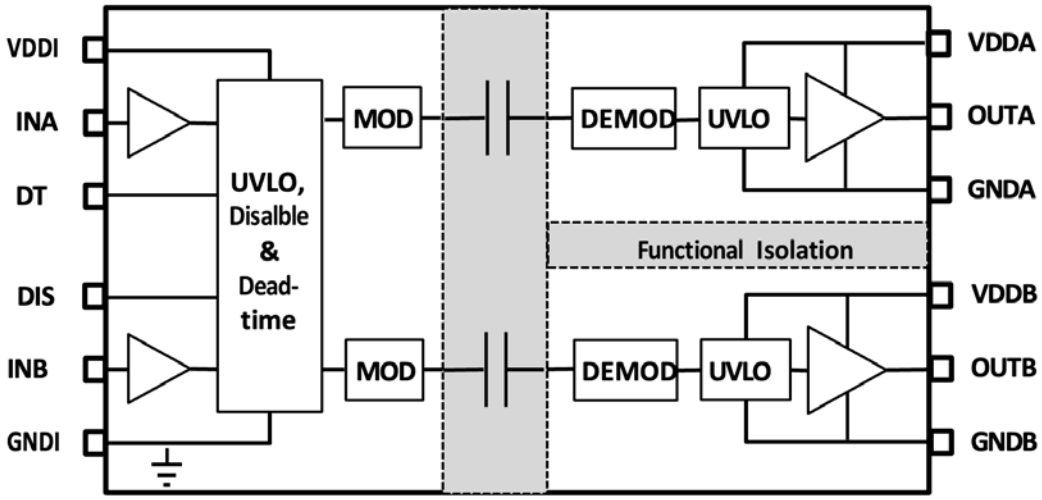
1. Features

- 4.0A peak source and 6.0A peak sink output current
- Input side supply voltage: 2.7V to 5.5V
- Driver side supply voltage: up to 30V with UVLO
- Rail-to-rail output voltage
- ±200kV/us minimum common mode rejection at VCM=1500V
- 25ns typical propagation delay
- Minimum input pulse width 20ns
- UVLO with hysteresis
- Programmable deadtime
- DIS function for disabling the out puts.
- 5ns maximum delay matching
- Operation temperature range: -40℃ to 105℃
- Safety certifications: (Planned)
  - 5kVRMS isolation for 1 minute per UL 1577 with SOW16 package
  - DIN EN IEC 60747-17 (VDE 0884-17):2021-10

2. Applications

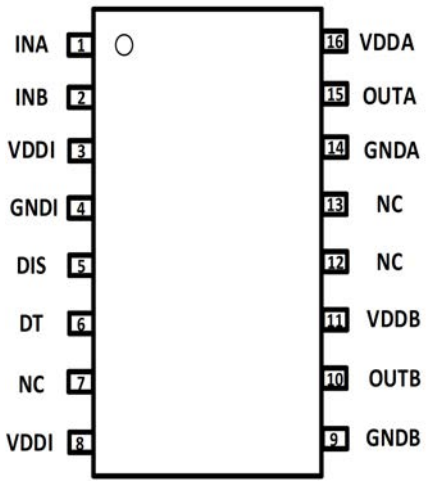
- IGBT/MOSFET gate drive
- AC & Brushless DC Motor Drives
- Renewable energy inverters
- AC/DC or DC/DC power supplies
- Industrial inverters
- Switching power supply

3. Functional Diagram



4. Pin Definition

No.	Symbol	Description
1	INA	TTL/CMOS compatible input signal for channel A with internal pull down to GND.
2	INB	TTL/CMOS compatible input signal for channel B with internal pull down to GND.
3,8	VDDI	Input side supply voltage.
4	GND	Input side ground reference.
5	DISABLE	Disable the isolator inputs and driver outputs if asserted high, enable if asserted low or left open
6	DT	Programmable deadtime control.
9	GNDB	Ground for output channel B
10	OUTB	Output gate driver for channel B
11	VDDB	Supply voltage for channel B
14	GNDA	Ground for output channel A
15	OUTA	Output gate driver for channel A
16	VDDA	Supply voltage for channel A
7,12,13	NC	Not connected



SOW16/SOP16 Package

5. Product Family

Part Number	Peak Current	UVLO	DT	DIS	Package
IGD8233AW	+4.0A/-6.0A	6.5V/6.85V	Y	Y	SOW16
IGD 8233BW	+4.0A/-6.0A	8.5V/8.0V	Y	Y	SOW16
IGD 8233CW	+4.0A/-6.0A	13.2V/12.2V	Y	Y	SOW16
IGD 8233AS	+4.0A/-6.0A	6.5V/6.85V	Y	Y	SOP16
IGD 8233BS	+4.0A/-6.0A	8.5V/8.0V	Y	Y	SOP16
IGD 8233CS	+4.0A/-6.0A	13.2V/12.2V	Y	Y	SOP16

6. Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Unit
Input Side Supply Voltage	VDDI to GNDI	-0.3	6	V
Input Signal Voltage	V_{IA}, V_{IB}, V_{DIS}	-0.3	6	
Output Side Supply Voltage	VDDA to GNDA, VDDB to GNDB	-0.3	30	
Channel A to Channel B Isolation Voltage	V_{ISOAB}	-	1500	
Electrostatic discharge	HBM	-4000	4000	
	CDM	-1500	1500	
Storage Temperature	T_S	-65	+150	℃
Junction Temperature	T_j	-40	+150	℃

Note : VDDI, VIA, VIB, VDIS are reference to GNDI; VDDA, VOUTA is referenced to GNDA; VDDB, VOUTB is referenced to GNDB.

7. Recommended Operating Conditions

Parameter	Symbol	Min.	Max.	Unit
Input Side Supply Voltage	VDDI to GNDI	3.0	5.5	V
Input Signal Voltage	V_{IA}, V_{IB}, V_{DIS}	3.0	5.5	
Output Supply Voltage	VDDA to GNDA, VDDB to GNDB	7	20	
Input Signal Voltage	INA, INB, DIS,DT	0	V_{VDDI}	
Junction Temperature	Tj	-40	150	
Operating Temperature	TA	-40	125	℃

NOTE: Operation beyond recommended operating conditions may cause long term reliability issue or even damage to the IC.

8. Electrical Characteristics (DC)

VDDI=3.3V or 5V, VDDA=VDDB=12V for IGD8233A/B, VDDA=VDDB=15V for RM8233C, Ta=-40~125℃. Unless otherwise noted, typical values are tested at Ta=25℃

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Current leakage characteristics						
VDDI Quiescent Current	I_{VDDIQ}	-	0.4	2	mA	INA=0, INB=0
VDDI Operating Current	I_{VDDI}	-	11		mA	Input frequency 500kHz
VDDA/B Quiescent Current, per Channel	I_{VDDAQ}, I_{VDDBQ}	-	1.5	2.5	mA	INA=0,INB=0, VDDx=12V for 6V, 8V UVLO; VDDx=15V for 13V UVLO
VDDA/B Operation Current, per Channel	I_{VDDA}, I_{VDDB}	-	2.6	-	mA	100pF, 500KHz, VDDx=12V for 6V, 8V UVLO; VDDx=15V for 13V UVLO
UVLO						
VDDI UVLO Rising Threshold	V_{VDDI_ON}	2.35	2.55	2.75	V	
VDDI UVLO Falling Threshold	V_{VDDI_OFF}	2.15	2.35	2.55		
VDDI UVLO Hysteresis	V_{VDDI_HYS}	-	0.2	-		
VDDA/B UVLO Rising Threshold	V_{VDDO_ON}	5.7	6.15	6.5		IGD8233A(6V)
VDDA/B UVLO Falling Threshold	V_{VDDO_OFF}	5.4	5.85	6.2		
VDDA/B UVLO Hysteresis	V_{VDDO_HYS}	-	0.3	-		
VDDA/B UVLO Rising Threshold	V_{VDDO_ON}	7.5	8.0	8.5		IGD 8233B(8V)
VDDA/B UVLO Falling Threshold	V_{VDDO_OFF}	7.0	7.5	8.0		
VDDA/B UVLO Hysteresis	V_{VDDO_HYS}	-	0.5	-		
VDDA/B UVLO Rising Threshold	V_{VDDO_ON}	12.7	13.2	13.7		IGD 8233C(13V)
VDDA/B UVLO Falling Threshold	V_{VDDO_OFF}	11.7	12.2	12.7		
VDDA/B UVLO Hysteresis	V_{VDDO_HYS}	-	1	-		

Input Side Characteristic						
Input Pin Pull Down Resistance, INA, INB	R_{INA_PD}, R_{INB_PD},	-	100	-	kΩ	
Input Pin Pull Down Resistance, DIS(EN)	R_{DIS_PD}	-	100	-	kΩ	
Logic High Input Threshold	V_{INA_H}, V_{INB_H}, V_{DIS_H}	-	1.45	2	V	
Logic Low Input Threshold	V_{INA_L}, V_{INB_L}, V_{DIS_L}	0.8	1.3	-		
Input Hysteresis	V_{INA_HYS}, V_{INB_HYS}, V_{DIS_HYS}	-	0.15	-		
Output Side Characteristic						
	V_{VDDA-}					

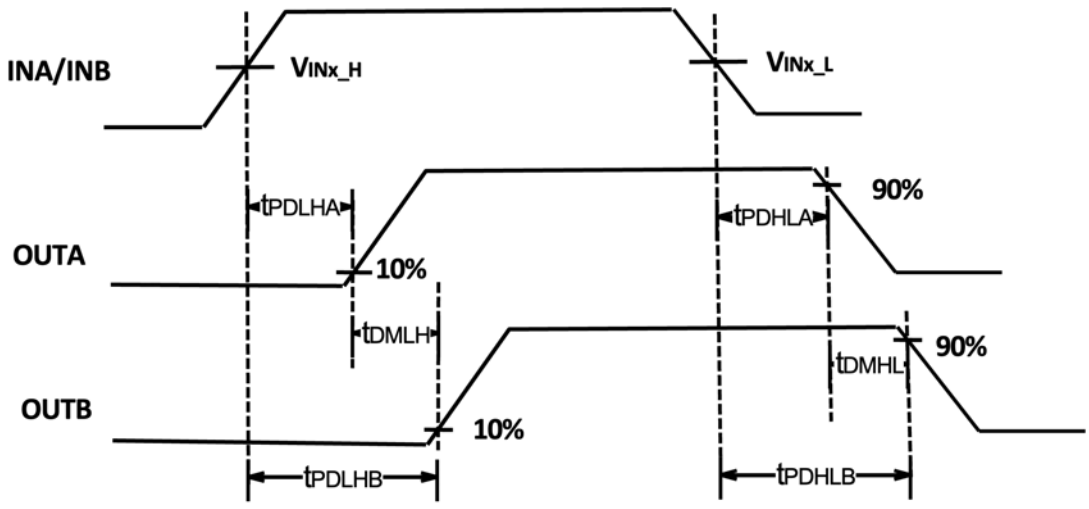
Logic High Output Voltage	V_{OUTA_H}, V_{VDDB-} V_{OUTB_H},	-	0.34	-	V	I_{out}=100mA
Logic Low Output Voltage	V_{OUTA_L}, V_{OUTB_L}	-	55	-	mV	I_{out}=100mA
Output Source Resistance	R_{OUTA_H}, R_{OUTB_H}	-	3.4	-	Ω	I_{out}=100mA
Output Sink Resistance	R_{OUTA_L}, R_{OUTB_L}	-	0.55	-	Ω	I_{out}=100mA
Peak Output Source Current	I_{OUTA+}, I_{OUTB+}	-	+4.0	-	A	VDDx=15V
Peak Output Sink Current	I_{OUTA-}, I_{OUTB-}	-	-6.0	-	A	VDDx=15V

9. Switching Characteristics (AC)

VDDI=3.3V or 5V, VDDA=VDDB=12V for RM8233A/B, VDDA=VDDB=15V for IGD8233C, Ta=25℃.

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Turn On Propagation Delay Time	t_{PDLH}	10	25	35	ns	$C_{OUTA/B}$=1 nF
Turn Off Propagation Delay Time	t_{PDHL}	10	25	35		$C_{OUTA/B}$=1 nF
Output Rise Time (20% to 80%)	t_R	-	7	16		$C_{OUTA/B}$=1.8nF, verified by design
Output Fall Time (90% to 10%)	t_F	-	6	12		$C_{OUTA/B}$=1.8nF, verified by design
Minimum Pulse Width	t_{PWmin}	-	10	15		$C_{OUTA/B}$=0 pF
Pulse Width Distortion $\|t_{PDHL}- t_{PDLH}\|$	t_{PWD}	-	-	6		
Channel to Channel Delay Matching	t_{DMLH}, t_{DMHL}	-	-	5		
Programmed Deadtime	t_{DT}	160	200	240		t_{DT}(ns)=10*R(KΩ); Test for R=20KΩ
Shutdown Time from Disable True	t_{DIS}	-	-	40		
Recovery Time from Disable False	T_{EN}	-	-	40		
VDDI Power-up Time Delay (Time from VDDI=VDDI_ON to OUTA/B=INA/B)	t_{start_VDDI}	-	8.5	15	us	INA or INB tied to VDDI
VDDA/B Power-up Time Delay (Time from VDDA/B=2V to OUTA/B=INA/B)	t_{start_VDDA}, t_{start_VDDB}	-	18	30	us	INA or INB tied to VDDI $C_{OUTA/B}$=1.8nF
High Level Common Mode Transient Immunity	$CMTI_H$	100	150	-	kV/us	
Low Level Common Mode Transient Immunity	$CMTI_L$	100	150	-	kV/us	

Propagation Delay and Delay Match Time



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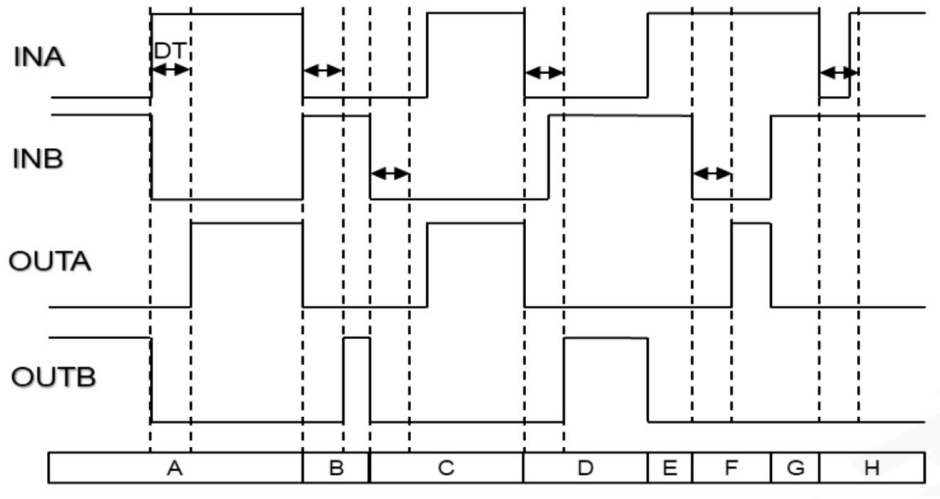
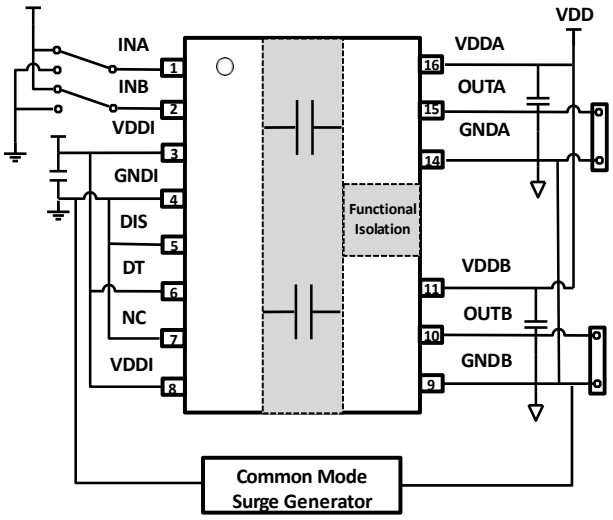
Input and Output Logic with Programmed Deadtime



CMTI Test Circuit



10. Feature Description

IGD8233 is a flexible dual channel isolated gate driver that can drive IGBTs and MOSFETs. It has 4.0A peak output current capability with maxim output driver supply voltage of 30V. It has many features that allow it to integrate well with control circuitry and protect the gates it drives such as: resistor programmable dead time control, an DIS pin, and under voltage lock out (UVLO) for both input and output voltages.

Under Voltage Lockout

The IGD8233 has under voltage lock out (UVLO) protection feature on each driver power supply voltage between the VDDA (VDDB) and GNDA (GNDB) pins. When the VDDx voltage is lower than VUVLO_VDDX_R, during device start up or lower than VUVLO_VDDX_F, after starting up, the VDDA (VDDB) UVLO feature holds the driver output low, regardless of the status of the input pins. A hysteresis on the UVLO feature prevents glitch when there is noise from the power supply. The IGD8233 also monitors the input power supply and there is an internal under voltage lock out protection feature on the VDDI. The driver outputs (OUTA and OUTB) are hold low when the voltage on the VDDI is lower than VUVLO_VDDI_R during start up or lower than VUVLO_VDDI_F after starting up. There is a hysteresis on the VDDI UVLO feature to prevent glitch due the noise on the VDDI power supply.

Disable Input Function

When the DIS is pulled high, the OUTA and OUTB are pulled low regardless of the states of INA and INB. When the DIS pin is pulled low, the VOA and VOB are allowed for normal operation and controlled by the INA and INB.

The DIS input has no effect if VDDI is below its UVLO threshold and OUTA, OUTB remain low. There is an internal pull-down resistor on the DIS pin.

Control Input and Output Logic

The INA and INB input controls the corresponding output channel, OUTA and OUTB. A logic high signal on INA (INB) causes the output of OUTA (OUTB) to go high. And a logic low on INA (INB) causes the output of OUTA (OUTB) to go low.

Truth table

INA	INB	DIS	VDDI UVLO	VDDA UVLO	VDDB UVLO	OUTA	OUTB	Notes
H	L	L	NO	NO	X	H	L	
L	H	L	NO	X	NO	L	H	
L	L	L	NO	X	X	L	L	
H	H	L	NO	NO	NO	H	H	Dual driver
H	H	L	NO	NO	NO	L	L	Half bridge
X	X	H	NO	NO	NO	L	L	Device disabled
X	X	X	YES	NO	NO	L	L	VDDI UVLO activated
X	H	L	NO	YES	X	L	X	VDDA UVLO activated
H	X	L	NO	NO	YES	X	L	VDDB UVLO activated

Dead-time Program

For the high side/low side configuration driver, there is a dead-time between OUTA and OUTB. The dead-time delay (tDT) is programmed by a resistor (RDT) connected from the DT input to ground and it can be calculated with below equation.

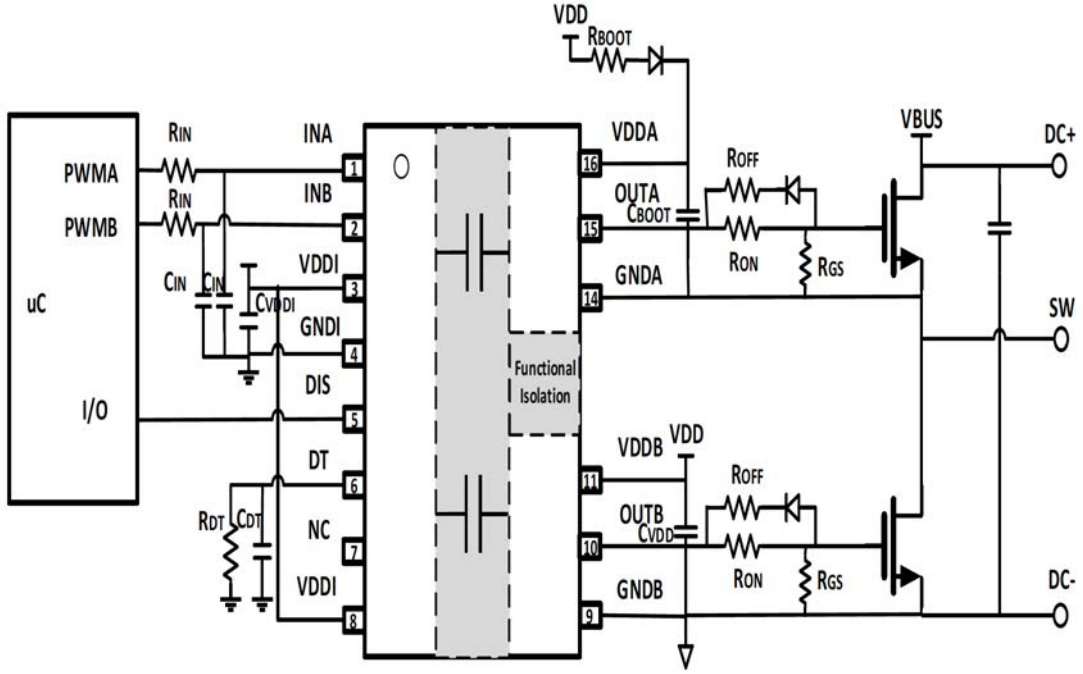
$$tDT\ [\mathrm{ns}] \approx 10 \times RDT\ [\mathrm{k\Omega}]$$

Here, tDT is the dead-time delay, RDT is the resistance value between DT and ground.

The DT pin can be connected to VDDI or left floating to provide a nominal dead time at approximately 10 ns.

A bypassing capacitor is recommended to be put between DT and GNDI to achieve better noise immunity.

11. Application Information



Recommended Design

Parameter	Value	Units
VDDI	5	V
VDDA/VDDB	12	V
Input signal amplitude	5	V
Switching frequency(fs)	10~100	KHz
Dead time	200	nS
RDT	20	kΩ
CDT	2.2	nF
RIN	51	Ω
CIN	33	pF
RON	10	Ω
ROFF	-	Ω
RBOOT	22	Ω
RGS	10	kΩ
CVDDI	10	uF
CVDD	10	uF
CBOOT	10	uF

12. Insulation Characteristics

SOW16 Insulation Characteristics

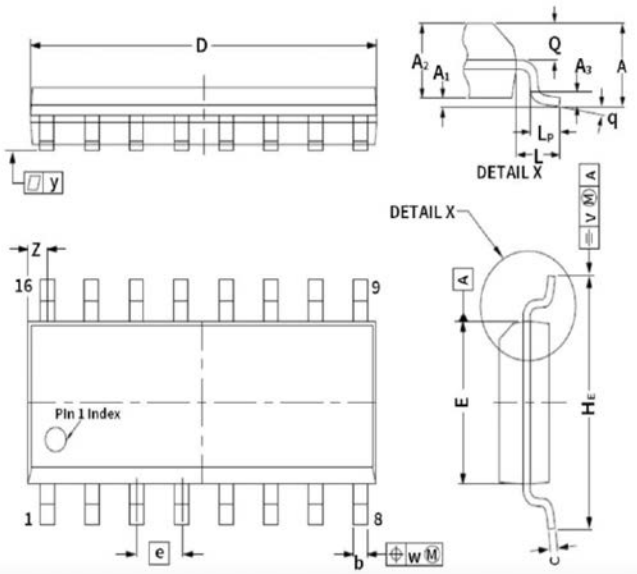
	Value	Note
Installation class:		
mains≤ 150Vrms	I-IV	
mains≤ 300Vrms	I-IV	
mains≤ 600Vrms	I-IV	
mains≤ 1000Vrms	I-III	
climatic class	40/125/21	
pollution degree	2	
Clearance (mm)	8	
Creepage (mm)	8	
DTI(um)	>20	
CTI	600	
DIN EN IEC 60747-17 (VDE 0884-17):2021-10		
V_{IORM} (Vpeak)	1420	
V_{PR} (Vpeak)	2272	Method A, VPR = 1.6xV_{IORM}, 1s ,qpd< 5pC
V_{PR} (Vpeak)	2663	Method B, VPR = 1.875xV_{IORM}, 1s ,qpd< 5pC
V_{IOTM} (Vpeak)	5000	
V_{IOSM} (Vpeak)	5000	
RIO (ohms)	>10e9	
UL1577		
V_{ISO} 1min (Vrms)	5700	
V_{ISO} 1s (Vrms)	6840	

SOP16 Insulation Characteristics

	Value	Note
Installation class:		
mains≤ 150Vrms	I-IV	
mains≤ 300Vrms	I-IV	
mains≤ 600Vrms	I-IV	
mains≤ 1000Vrms	I-III	
climatic class	40/125/21	
pollution degree	2	
Clearance (mm)	8	
Creepage (mm)	8	
DTI(um)	>20	
CTI	600	
DIN EN IEC 60747-17 (VDE 0884-17):2021-10		
V_{IORM} (Vpeak)	900	
V_{PR} (Vpeak)	1440	Method A, VPR = 1.6xV_{IORM}, 1s ,qpd< 5pC
V_{PR} (Vpeak)	1687	Method B, VPR = 1.875xV_{IORM}, 1s ,qpd< 5pC
V_{IOTM} (Vpeak)	3000	
V_{IOSM} (Vpeak)	3000	
RIO (ohms)	>10e9	
UL1577		
V_{ISO} 1min (Vrms)	3000	
V_{ISO} 1s (Vrms)	4200	

13. Package Information

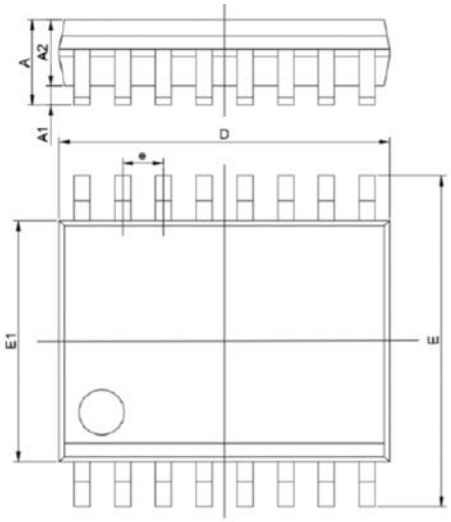
SOP16 package

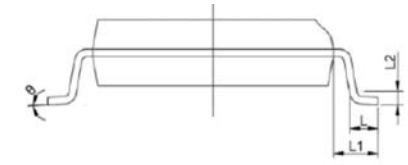


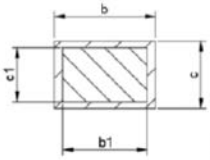
* CONTROLLING DIMENSION:MM

SYMBOL	MILLIMETER			INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	---	---	1.75	---	---	0.069
A1	0.10	---	0.25	0.004	---	0.010
A2	1.25	---	1.45	0.049	---	0.057
b	0.36	---	0.49	0.014	---	0.019
c	0.19	---	0.25	0.007	---	0.010
D	9.80	9.90	10.0	0.386	0.390	0.394
E	3.80	3.90	4.00	0.150	0.154	0.158
HE	5.80	---	6.20	0.228	---	0.244
Q	0.60	---	0.70	0.024	---	0.028
e	1.27 bsc			0.050 bsc		
L	1.05 bsc			0.041 bsc		
Lp	0.40	---	1.00	0.016	---	0.039
Y	---	0.10	---	---	0.004	---
A3	---	0.25	---	---	0.010	---
Z	0.30		0.70	0.012		0.028
θ	0°	---	8°	0°	---	8°

SOW16 package







Dimension	MIN	MAX
A	-	2.65
A1	0.1	0.3
A2	2.05	-
b	0.31	0.51
b1	0.27	0.48
c	0.1	0.33
c1	0.1	0.3
E	10.3BASIC	
E1	7.5BASIC	
e	1.27BASIC	
L	0.4	1.27
L1	1.4REF	
L2	0.25BASIC	
θ	0	8
D	10.3	